What Is Claimed Is:

- A pedestal supporting a substrate in a plasma chamber,
- 2 comprising:
- 3 an insulating base;
- a conductive layer on the insulating base; and
- 5 a ceramic cover at least partially covering the conductive
- 6 layer, the conductive layer being covered when the
- 7 pedestal supports a substrate.
- 1 2. The pedestal in claim 1, wherein the conductive layer
- 2 further comprises a bottom portion with a bottom width and an
- 3 upper portion with an upper width, the upper width being less
- 4 than the bottom width and a diameter of the substrate.
- 1 3. The pedestal in claim 2, wherein the insulating base
- 2 further comprises a recess accommodating the bottom portion of
- 3 the conductive layer.
- 1 4. The pedestal in claim 1, wherein the ceramic cover
- 2 further overlies the insulating base.

- 1 5. The pedestal in claim 1, wherein the ceramic cover
- 2 further comprises an opening exposing the conductive layer.
- 1 6. The pedestal in claim 2, wherein the ceramic cover
- 2 overlies the bottom portion of the conductive layer and further
- 3 comprises a hollow portion accommodating the upper portion of
- 4 the conductive layer.
- 7. The pedestal in claim 1, wherein the ceramic cover is
- 2 ring-shaped.
- 1 8. The pedestal in claim 1, wherein the insulating base
- 2 comprises silicon oxide.
- 1 9. The pedestal in claim 1, wherein the conductive layer
- 2 comprises titanium.
- 1 10. The pedestal in claim 1, wherein the ceramic cover
- 2 comprises aluminum oxide.

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- 11. A pedestal supporting a substrate in a plasma chamber,
- 2 comprising:
- 3 an insulating base having a recess;

- a conductive layer embedded in the recess; and
- a ceramic cover overlying the insulating base and partially
- 6 covering the conductive layer;
- 7 wherein the conductive layer is covered when the pedestal
- 8 supports a substrate.
- 1 12. The pedestal in claim 11, wherein the conductive layer
- 2 further comprises an upper portion, with a width less than the
- diameter of the substrate, protruding from the recess.
- 1 13. The pedestal in claim 11, wherein the conductive layer
- 2 further comprises an upper portion, with a width less than the
- 3 diameter of the substrate and the width of the other portion of
- 4 the conductive layer, protruding from the recess.
- 1 14. The pedestal in claim 13, wherein the ceramic cover
- 2 further comprises a hollow portion accommodating the upper
- 3 portion of the conductive layer.
- 1 15. The pedestal in claim 13, wherein the ceramic cover
- 2 further comprises a hollow portion accommodating the upper

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- 3 portion of the conductive layer and exposing the narrower upper
- 4 portion of the conductive layer.
- 1 16. The pedestal in claim 11, wherein the ceramic cover
- 2 is ring-shaped.
- 1 17. The pedestal in claim 11, wherein the insulating base
- 2 comprises silicon oxide.
- 1 18. The pedestal in claim 11, wherein the conductive layer
- 2 comprises titanium.
- 1 19. The pedestal in claim 11, wherein the ceramic cover
- 2 comprises aluminum oxide.
- 1 20. A pedestal supporting a substrate in a plasma chamber,
- 2 comprising:
- a silicon-oxide base having a recess;
- a titanium layer having a bottom portion embedded in the
- 5 recess, and an upper portion, narrower than the
- 6 bottom portion and the substrate, protruding from the
- 7 recess; and

- a ring-shaped ceramic cover, having a hollow portion

 accommodating the upper portion of the titanium layer

 therein, overlying the insulating base and a portion

 of the bottom portion of the titanium layer;

 wherein the conductive layer is covered when the pedestal

 supports the substrate.
 - 1 21. The method as claimed in claim 20, wherein the hollow 2 portion of the ceramic cover further exposes the upper portion 3 of the titanium layer.
 - 1 22. The pedestal in claim 20, wherein the ceramic cover comprises aluminum oxide.